



10/614/60

COFC
CL

PTO/SB/17 (12-04v2)

Approved for use through 7/31/2006. OMB 0651-0032
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no person are required to respond to a collection of information unless it displays a valid OMB control number.

Effective on 12/08/2004. Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).		Complete if Known	
FEE TRANSMITTAL For FY 2005		Application Number	Patent#: 6,961,277
		Filing Date	Issued: November 1, 2005
		First Named Inventor	John T. Moore
		Examiner Name	V. Q. Nguyen
		Art Unit	2818
<input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27		Attorney Docket No.	M4065.0715/P715
TOTAL AMOUNT OF PAYMENT (\$) 100.00			

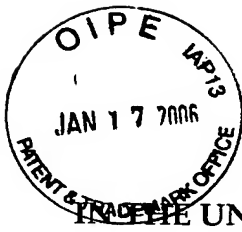
METHOD OF PAYMENT (check all that apply)	
<input type="checkbox"/> Check	<input checked="" type="checkbox"/> Credit Card
<input type="checkbox"/> Money Order	<input type="checkbox"/> None
<input type="checkbox"/> Other (please identify): _____	
<input type="checkbox"/> Deposit Account	Deposit Account Number: <u>04-1073</u> Deposit Account Name: <u>Dickstein Shapiro Morin & Oshinsky LLP</u>
For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)	
<input checked="" type="checkbox"/> Charge fee(s) indicated below	<input type="checkbox"/> Charge fee(s) indicated below, except for the filing fee
<input type="checkbox"/> Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17	<input checked="" type="checkbox"/> Credit any overpayments

FEE CALCULATION							
1. BASIC FILING, SEARCH, AND EXAMINATION FEES							
	FILING FEES		SEARCH FEES		EXAMINATION FEES		
		Small Entity		Small Entity		Small Entity	
Application Type	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fees Paid (\$)
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	
2. EXCESS CLAIM FEES							
						Fee (\$)	Small Entity Fee (\$)
Fee Description							
Each claim over 20 (including Reissues)						50	25
Each independent claim over 3 (including Reissues)						200	100
Multiple dependent claims						360	180
Total Claims		Extra Claims	Fee (\$)	Fee Paid (\$)	Multiple Dependent Claims		
_____ - = _____		x _____	= _____		Fee (\$) Fee Paid (\$)		
Indep. Claims		Extra Claims	Fee (\$)	Fee Paid (\$)			
_____ - = _____		x _____	= _____				
3. APPLICATION SIZE FEE							
If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).							
Total Sheets	Extra Sheets	Number of each additional 50 or fraction thereof		Fee (\$)	Fee Paid (\$)		
_____ - 100 = _____	/50	_____ (round up to a whole number) x _____		= _____			
4. OTHER FEE(S)							
						Fees Paid (\$)	
Non-English Specification, \$130 fee (no small entity discount)							
Other (e.g., late filing surcharge): <u>1811 Certificate of correction</u>						100.00	

SUBMITTED BY			
Signature		Registration No. (Attorney/Agent)	28,371
Name (Print/Type)	Thomas J. D'Amico	Telephone	(202) 828-2232
		Date	January 17, 2006

Certificate
JAN 20 2006
of Correction

FEB 1 2006



Docket No.: M4065.0715/P715
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
John T. Moore et al.

Patent No.: 6,961,277

Issued: November 1, 2005

For: METHOD OF REFRESHING A PCRAM
MEMORY DEVICE

**REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 C.F.R. §§ 1.322 & 1.323**

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted omissions and typographical errors which should be corrected.

In the **U.S. Patent Documents** portion of the References Cited section, the USPTO omitted the listing of forty-nine patents. Exhibit A, attached, shows the IDS forms as considered and signed by the Examiner. The patents that should be added are as follows:

3,622,319	11/1971	Sharp	01/19/2006 MBEYENE1 00000039 6961277 FC:1811 100.00 OP
3,743,847	7/1973	Boland	
4,269,935	5/1981	Masters et al.	

FEB 1 2006

4,312,938	1/1982	Drexler, et al.
4,316,946	1/1982	Masters, et al.
4,320,191	3/1982	Yoshikawa et al.
4,405,710	9/1983	Balasubramanyam et al.
4,419,421	12/1983	Wichelhaus, et al.
4,499,557	2/1985	Holmberg et al.
4,671,618	06/09/1987	Wu et al.
4,795,657	1/1989	Formigoni et al.
4,800,526	01/24/1989	Lewis
4,847,674	7/1989	Sliwa et al.
5,219,788	6/1993	Abernathey et al.
5,238,862	8/1993	Blalock et al.
5,272,359	12/21/1993	Nagasubramanian et al.
5,314,772	5/24/1994	Kozicki
5,315,131	5/1994	Kishimoto et al.
5,350,484	9/1994	Gardner et al.
5,360,981	11/1994	Owen et al.
5,500,532	3/19/1996	Kozicki et al.
5,512,328	4/1996	Yoshimura et al.
5,512,773	4/1996	Wolf et al.
5,726,083	3/1998	Takaishi
5,751,012	5/12/1998	Wolstenholme et al.
5,761,115	6/1998	Kozicki et al.

5,769,277	8/1998	Zahorik et al.
5,814,527	9/29/1998	Wolstenholme et al.
5,818,749	10/06/1998	Harshfield
5,841,150	11/1998	Gonzalez et al.
5,846,889	12/1998	Harbison et al.
5,851,882	12/22/1998	Harshfield
5,869,843	2/9/1999	Harshfield
5,896,312	4/20/1999	Kozicki et al.
5,914,893	6/22/1999	Kozicki et al.
5,920,788	7/1999	Reinberg
5,998,066	12/1999	Block et al.
6,031,287	2/29/2000	Harshfield
6,072,716	06/06/2000	Jacobson et al.
6,077,729	6/2000	Harshfield
6,084,769	7/4/2000	Kozicki et al.
6,177,338	1/2001	Liaw et al.
6,117,720	9/2000	Harshfield
6,143,604	11/2000	Chiang et al.
6,236,059	5/2001	Wolstenholme et al.
6,297,170	10/2001	Gabriel et al.
6,300,684	10/2001	Gonzalez et al.
6,316,684	11/2001	Zahorik et al.
6,511,867	1/2003	Lowery et al.

In the **Other Publications** portion of the References Cited section, the USPTO made the following errors to be corrected:

“Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RgAg₄I₅. Solid State Ionics 70/71 (1994) 72-76.”

Should read

--Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg₄I₅. Solid State Ionics 70/71 (1994) 72-76.--;

“Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature electric field induced creation of stable devices in CuInSe₂ Crystals, Science 258 (1992) 271-271.”

Should read

--Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature electric field induced creation of stable devices in CuInSe₂ Crystals, Science 258 (1992) 271-271.--;

“El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag_{2-x}Se_{1+x/n}-Si diodes, Thin Solid Films 110 (1983) 107-113.”

Should read

--El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag_{2-x}Se_{1+x/n}-Si diodes, Thin Solid Films 110 (1983) 107-113.--; and

“West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag|As_{0.24}S_{0.36}Ag_{0.40}|Ag systems prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974.”

Should read

--West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag|As_{0.24}S_{0.36}Ag_{0.40}|Ag systems prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974.--.

Also in **Other Publications**, Applicants made the following errors to be corrected:

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."

Should read

--Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.--;

"McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f."

Should read

--McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987).--;

"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a-Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080."

Should read

--Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.--; and

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Despert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985."

Should read

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Despert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural

investigation, Transport-structure relations in fast ion and mixed conductors, Proceedings of the 6th RISO International symposium, Sep. 9-13, 1985."

In the **Specification**, Applicants made the following errors to be corrected:

Column 11, line 6, "900 include" should read --900 includes--; and

Column 11, line 56, "system" should read --systems--.

In the **Claims**, Applicants made the following error to be corrected:

Claim 12, column 13, line 33, "a erase" should read --an erase--.

Some errors were found in the application as filed by applicant but most were made by the USPTO. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentees respectfully solicit the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-107A duplicate copy of this paper is enclosed.

Dated: January 17, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Ryan H. Flax

Registration No.: 48,141

DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicants



Exhibit A

FEB 1 2006

DEC 02 2003

JAN 17 2006

PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0851-0031

U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2 of 11

Complete if Known

Application Number	10/614,160
Filing Date	July 8, 2003
First Named Inventor	John T. Moore, et al.
Art Unit	4810 2827
Examiner Name	Not Yet Assigned V. Nguyen
Attorney Docket Number	M4065.0715/P715

W	AU1	3,622,319	11/1971	Sharp	
W	AV1	3,743,847	7/1973	Boland	
	AW1	4,269,935	5/1981	Masters et al.	
	AX1	4,312,938	1/1982	Drexler, et al.	
	AY1	4,316,946	1/1982	Masters, et al.	
	AZ1	4,320,191	3/1982	Yoshikawa et al.	
	AA2	4,405,710	9/1983	Balasubramanyam et al.	
	AB2	4,419,421	12/1983	Wichelhaus, et al.	
	AC2	4,499,557	2/1985	Holmberg et al.	
	AD2	4,671,618	06/09/1987	Wu et al.	
	AE2	4,795,657	1/1989	Formigoni et al.	
	AF2	4,800,526	01/24/1989	Lewis	
	AG2	4,847,674	7/1989	Silwa et al.	
	AH2	5,477,567	1/1993	Kersey et al.	
	AI2	5,219,788	6/1993	Abermathey et al.	
	AJ2	5,238,862	8/1993	Blalock et al.	
	AK2	5,272,359	12/21/1993	Nagasubramanian et al.	
	AL2	5,314,772	5/24/1994	Kozicki	
	AM2	5,315,131	5/1994	Kishimoto et al.	
	AN2	5,350,484	9/1994	Gardner et al.	
	AO2	5,360,981	11/1994	Owen et al.	
	AP2	5,500,532	3/19/1996	Kozicki et al.	
	AQ2	5,512,328	4/1996	Yoshimura et al.	
	AR2	5,512,773	4/1996	Wolf et al.	
	AS2	5,726,083	3/1998	Takaishi	
	AT2	5,751,012	5/12/1998	Wolstenholme et al.	
	AU2	5,761,115	6/1998	Kozicki et al.	
	AV2	5,789,277	8/1998	Zahorik et al.	
	AW2	5,814,527	9/29/1998	Wolstenholme et al.	
	AX2	5,818,749	10/06/1998	Harshfield	
	AY2	5,841,150	11/1998	Gonzalez et al.	
	AZ2	5,846,889	12/1998	Harbison et al.	
	AA3	5,851,882	12/22/1998	Harshfield	
	AB3	5,869,843	2/9/1999	Harshfield	
	AC3	5,896,312	4/20/1999	Kozicki et al.	
	AD3	5,914,893	6/22/1999	Kozicki et al.	
	AE3	5,920,788	7/1999	Reinberg	
	AF3	5,998,066	12/1999	Block et al.	
	AG3	6,031,287	2/29/2000	Harshfield	
	AH3	6,072,716	06/06/2000	Jacobson et al.	
	AI3	6,077,729	6/2000	Harshfield	
	AJ3	6,084,796	7/4/2000	Kozicki et al.	
	AK3	6,177,338	1/2001	Llaw et al.	
	AL3	6,117,720	9/2000	Harshfield	
	AM3	6,143,604	11/2000	Chiang et al.	
	AN3	6,238,059	5/2001	Wolsteinholme et al.	
	AO3	6,297,170	10/2001	Gabriel et al.	
	AP3	6,300,684	10/2001	Gonzalez et al.	
	AQ3	6,316,784	11/2001	Zahorik et al.	

1695747 v1: 10CG3011.DOC

All but one omitted on
printed patent

 VIET Q. NGUYEN
PRIMARY EXAMINER

FEB 1 2006

6/2/05

Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/B/PTO			Complete If Known 10/6/14, 160	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Application Number	4065.0715 Conf. #8479
			Filing Date	July 8, 2003
			First Named Inventor	John T. Moore
			Art Unit	2827 2827
			Examiner Name	Not Yet Assigned
			Attorney Docket Number	M4065.0715/P715
Sheet	2	of	3	

P1	US 5,335,219	8/1994	Ovshinsky et al.	
Q1	US 5,359,205	10/1994	Ovshinsky	
R1	US 5,341,328	8/1994	Ovshinsky et al.	
S1	US 5,408,509	4/1995	Ovshinsky et al.	
T1	US 5,414,271	5/1995	Ovshinsky et al.	
U1	US 5,534,711	7/1996	Ovshinsky et al.	
V1	US 5,534,712	7/1996	Ovshinsky et al.	
W1	US 5,536,947	7/1996	Kiersy et al.	
X1	US 5,543,737	8/1996	Ovshinsky	
Y1	US 5,591,501	1/1997	Ovshinsky et al.	
Z1	US 5,596,522	1/1997	Ovshinsky et al.	
A2	US 5,687,112	11/1997	Ovshinsky	
B2	US 5,694,054	12/1997	Ovshinsky et al.	
C2	US 5,714,768	2/1998	Ovshinsky et al.	
D2	US 5,825,046	10/1998	Czubatyj et al.	
E2	US 5,912,839	6/1999	Ovshinsky et al.	
F2	US 5,933,365	8/1999	Kiersy et al.	
G2	US 6,011,757	1/2000	Ovshinsky	
H2	US 6,087,674	7/2000	Ovshinsky et al.	
I2	US 6,141,241	10/2000	Ovshinsky et al.	
J2	US 6,339,544	1/2002	Chiang et al.	
K2	US 6,404,685	6/2002	Lowery et al.	
L2	US 6,429,084	8/2002	Wicker	
M2	US 6,437,383	8/2002	Xu	
N2	US 6,462,984	10/2002	Xu et al.	
O2	US 6,480,438	11/2002	Park	
P2	US 6,487,113	11/2002	Park et al.	
Q2	US 6,501,111	12/2002	Lowery	
R2	US 6,507,081	1/2003	Hudgens et al.	
S2	US 6,511,862	1/2003	Hudgens et al.	
T2	US 6,511,867	1/2003	Lowery et al.	
U2	US 6,512,241	1/2003	Lai	
V2	US 6,514,805	2/2003	Xu et al.	
W2	US 6,531,373	3/2003	Gill et al.	
X2	US 6,534,781	3/2003	Dennison	
Y2	US 6,545,287	4/2003	Chiang	
Z2	US 6,545,907	4/2003	Lowery et al.	
A3	US 6,555,860	4/2003	Lowery et al.	
B3	US 6,563,164	5/2003	Lowery et al.	
C3	US 6,566,700	5/2003	Xu	
D3	US 6,567,293	5/2003	Lowery et al.	
E3	US 6,568,705	5/2003	Chiang et al.	
F3	US 6,570,784	5/2003	Lowery	
G3	US 6,576,921	6/2003	Lowery	
H3	US 6,586,761	7/2003	Lowery	

VIET Q. NGUYEN
PRIMARY EXAMINER

* Omitted

VIET Q. NGUYEN
PRIMARY EXAMINER

FEB 1 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 5

PATENT NO. : 6,961,277
APPLICATION NO. : 10/614,160
ISSUE DATE : November 1, 2005
INVENTORS : John T. Moore et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the **U.S. Patent Documents** portion of the References Cited section, forty-nine patents should be added as follows:

3,622,319	11/1971	Sharp
3,743,847	7/1973	Boland
4,269,935	5/1981	Masters et al.
4,312,938	1/1982	Drexler, et al.
4,316,946	1/1982	Masters, et al.
4,320,191	3/1982	Yoshikawa et al.
4,405,710	9/1983	Balasubramanyam et al.
4,419,421	12/1983	Wichelhaus, et al.
4,499,557	2/1985	Holmberg et al.
4,671,618	06/09/1987	Wu et al.
4,795,657	1/1989	Formigoni et al.
4,800,526	01/24/1989	Lewis

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 1
2101 L Street NW
Washington, DC 20037-1526

FEB 1 2006

4,847,674	7/1989	Sliwa et al.
5,219,788	6/1993	Abernathey et al.
5,238,862	8/1993	Blalock et al.
5,272,359	12/21/1993	Nagasubramanian et al.
5,314,772	5/24/1994	Kozicki
5,315,131	5/1994	Kishimoto et al.
5,350,484	9/1994	Gardner et al.
5,360,981	11/1994	Owen et al.
5,500,532	3/19/1996	Kozicki et al.
5,512,328	4/1996	Yoshimura et al.
5,512,773	4/1996	Wolf et al.
5,726,083	3/1998	Takaishi
5,751,012	5/12/1998	Wolstenholme et al.
5,761,115	6/1998	Kozicki et al.
5,789,277	8/1998	Zahorik et al.
5,814,527	9/29/1998	Wolstenholme et al.
5,818,749	10/06/1998	Harshfield
5,841,150	11/1998	Gonzalez et al.
5,846,889	12/1998	Harbison et al.
5,851,882	12/22/1998	Harshfield
5,869,843	2/9/1999	Harshfield
5,896,312	4/20/1999	Kozicki et al.
5,914,893	6/22/1999	Kozicki et al.
5,920,788	7/1999	Reinberg
5,998,066	12/1999	Block et al.
6,031,287	2/29/2000	Harshfield
6,072,716	06/06/2000	Jacobson et al.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico

DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2

2101 L Street NW

Washington, DC 20037-1526

FEB 1 2006

6,077,729	6/2000	Harshfield
6,084,769	7/4/2000	Kozicki et al.
6,177,338	1/2001	Liaw et al.
6,117,720	9/2000	Harshfield
6,143,604	11/2000	Chiang et al.
6,236,059	5/2001	Wolstenholme et al.
6,297,170	10/2001	Gabriel et al.
6,300,684	10/2001	Gonzalez et al.
6,316,684	11/2001	Zahorik et al.
6,511,867	1/2003	Lowery et al.

In the **Other Publications** portion of the References Cited section, the following errors are corrected:

"Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RgAg415. Solid State Ionics 70/71 (1994) 72-76."

Should read

--Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg₄I₅. Solid State Ionics 70/71 (1994) 72-76.--;

"Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature electric field induced creation of stable devices in CuInSe₂ Crystals, Science 258 (1992) 271-271."

Should read

--Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature electric field induced creation of stable devices in CuInSe₂ Crystals, Science 258 (1992) 271-271.--;

"El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Propeties of Ag_{2-x}Se_{1+x}/n-Si diodes, Thin Solid Films 110 (1983) 107-113."

Should read

--El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag_{2-x}Se_{1+x}/n-Si diodes, Thin Solid Films 110 (1983) 107-113.--;

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 3
2101 L Street NW
Washington, DC 20037-1526

FEB 1 2006

"West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag|As_{0.24}S_{0.36}Ag_{0.40}|Ag systems prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974."

Should read

--West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag|As_{0.24}S_{0.36}Ag_{0.40}|Ag systems prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974.--

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."

Should read

--Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.--;

"McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f."

Should read

--McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987).--;

"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a-Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080."

Should read

--Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.--; and

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Despert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985."

Should read

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Despert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors, Proceedings of the 6th RISO International symposium, Sep. 9-13, 1985."

In the **Specification**, the following errors are corrected:

Column 11, line 6, "900 include" should read --900 includes--; and

Column 11, line 56, "system" should read --systems--.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 4
2101 L Street NW
Washington, DC 20037-1526

In the **Claims**, the following error is corrected:

Claim 12, column 13, line 33, "a erase" should read --an erase--.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 5
2101 L Street NW
Washington, DC 20037-1526

FEB 1 2006